

SEMICONDUCTOR PROCESS DEVICE AND REACTION CHAMBER THEREOF AND FILM LAYER DEPOSITION METHOD

ABSTRACT

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The present disclosure provides a reaction chamber of a semiconductor process device, the semiconductor process device and a film layer deposition method. The reaction chamber includes: a chamber body, a monitoring module, a deposition module and a control module; wherein the deposition module is configured to execute multiple deposition steps within a deposition period in
10 the chamber body; the monitoring module is connected with the chamber body, and configured to monitor brightness of a plasma light source generated in the chamber body when the deposition module executes each deposition step, and generate a first signal according to the brightness of the plasma light source; and the control module is connected with the monitoring module, and
15 configured to judge whether a thickness of a target film layer obtained after executing the multiple deposition steps is abnormal according to the first signal corresponding to at least one of the deposition steps, and if yes, execute an abnormality processing flow. By the adoption of the present disclosure, a deviation between the thickness of the target film layer and a target thickness can be improved.

20 (FIG.2)